

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Naoki SHIBATA, et al.

Serial No.: 10/725,380

Group Art Unit: 2818

Filing Date: December 3, 2005 Examiner: Vu, David

For: GROUP III NITRIDE COMPOUND SEMICONDUCTOR DEVICE AND METHOD
OF PRODUCING THE SAME

Commissioner for Patents
Alexandria, VA 22313-1450



INFORMATION DISCLOSURE STATEMENT

Sir:

Under the provisions of 37 CFR §1.97 through §1.99 and pursuant to applicant's duty of disclosure under 37 CFR §1.56, applicant respectfully brings the following documents cited in the enclosed Japanese Office Action dated December 14, 2004, and listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application. Copies of the listed documents are provided herewith for the convenience of the Examiner.

In compliance with the concise explanation requirement under 37 CFR §1.98(a)(3), as a concise statement of relevance, as it is presently understood by the individual designated in 35 U.S.C. §1.56(c) most knowledgeable about the content of the information, the undersigned attorney of record submits a translation of portions of an official action by a foreign examiner in which the reference was cited. The relevance to the pending U.S. patent application is that the reference was cited in a foreign patent application on the same subject matter. However, no independent analysis of the reference, the accuracy of the statement of the foreign examiner or the claims of the foreign application under the laws of that country or the United States relative to the subject matter claimed in the present application has been made, the present understanding of the contents thereof by the undersigned being based on the translation of the foreign examiner's comments submitted herewith.

This citation does not constitute an admission that the references are relevant or material to the claims. They are only cited as constituting related art of which the applicant is aware.

I hereby certify that each item of information contained in this Information Disclosure Statement was the first citation of that item by a foreign patent office in a counterpart foreign application, which occurred not more than three months prior to the filing of this statement.

A check in the amount of \$180.00 is submitted herewith.

It is respectfully requested that the listed references be carefully considered by the Examiner and formally made of record in this application.

Please charge any deficiencies in fees and credit any overpayment of fees to Attorney's Deposit Account No. 50-0481.

Respectfully submitted,

A handwritten signature in black ink, appearing to read "P. E. Miller".

Phillip E. Miller, Esq.
Registration No. 46,060

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Date: 2/24/05

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INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>			Docket Number (Optional) T36-163905M/RS		Application Number 10/725,380		
			Applicant(s) Naoki Shibata, et al.		Filing Date 12/03/03		Group Art Unit 2818
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
							
FOREIGN PATENT DOCUMENTS							
REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
	02-081482	03/22/1990	JAPAN			FBS	
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
		Japanese Office Action dated December 14, 2004 with English translation.					
		Heon Lee, et al. Growth of Thick GaN Films on RF Sputtered AlN Buffer Layer by Hydride Vapor Phase Epitaxy, Journal of Electric Materials, vol 26, No. 8 (1997) pp 898-902.					
EXAMINER			DATE CONSIDERED				